

Dual N-channel 40 V, 19 mΩ standard level MOSFET

10 December 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ of greater than 1 V at 175 $^\circ\text{C}$

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	24.2	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	38	W
Static charac	teristics FET1 and FET2					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	15.5	19	mΩ
Dynamic cha	racteristics FET1 and FE	T2				
Q _{GD}	gate-drain charge	$I_{D} = 10 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$	-	4.3	-	nC



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2	\Box	
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

6. Ordering information

Table 3.Ordering in	formation					
Type number	Package	ackage				
	Name	Description	Version			
BUK7K18-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K18-40E	71840E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	24.2	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	22	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 4	-	127	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	38	W
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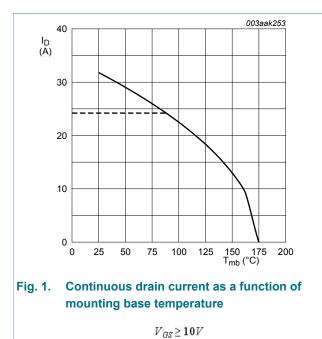
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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode FET1 and FET2					
I _S	source current	T _{mb} = 25 °C		-	24.2	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	127	А
Avalanche I	Ruggedness FET1 and FET2					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_{D} = 24.2 \text{ A}; V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; \underline{Fig. 3}$	[1][2]	-	26.3	mJ

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



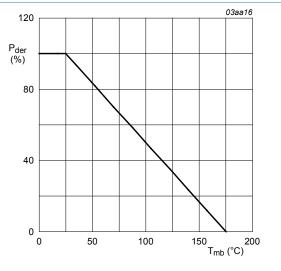
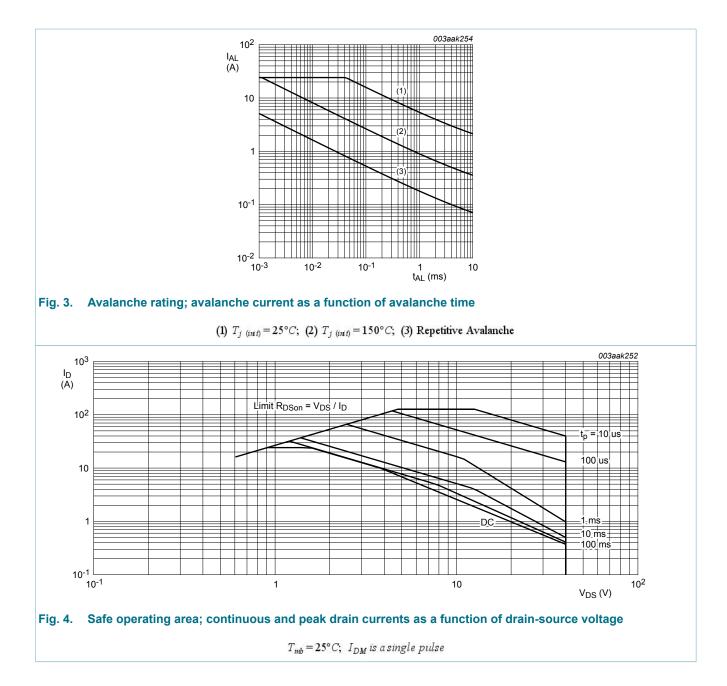


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

л –	P_{tot}	×100 %
$P_{der} =$	Ptot(25°C)	×100 %

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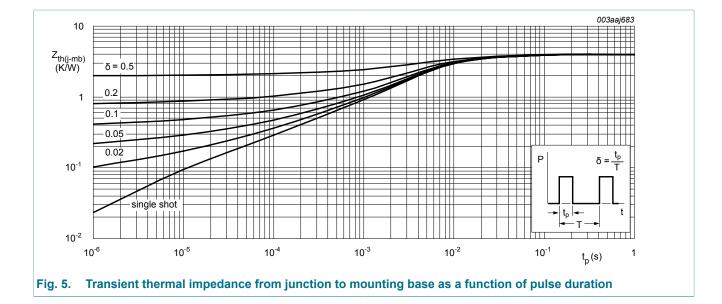


9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	3.96	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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10. Characteristics

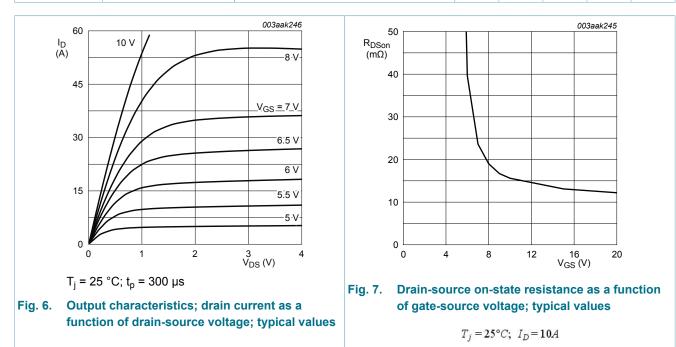
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2	· · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9; Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9; Fig. 10	-	-	4.5	V
I _{DSS}	s drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	15.5	19	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	30.5	37.4	mΩ
Dynamic ch	naracteristics FET1 and FE	T2	1			
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	11.8	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	3.6	-	nC
Q _{GD}	gate-drain charge	1	-	4.3	-	nC

Product data sheet

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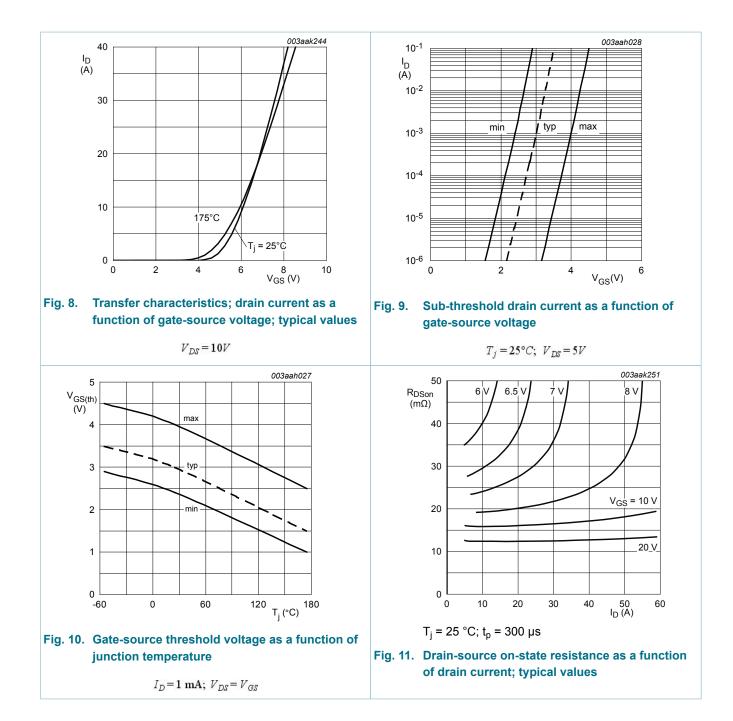
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;		-	606	808	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	134	161	pF
C _{rss}	reverse transfer capacitance			-	87	119	pF
t _{d(on)}	turn-on delay time	$\begin{split} V_{DS} &= 32 \text{ V}; \text{ R}_{L} = 3.3 \Omega; V_{GS} = 10 \text{ V}; \\ \text{ R}_{G(ext)} &= 5 \Omega; T_{j} = 25 ^{\circ}\text{C}; I_{D} = 10 A \end{split}$		-	6.2	-	ns
t _r	rise time			-	12.7	-	ns
t _{d(off)}	turn-off delay time	-		-	7.9	-	ns
t _f	fall time	-		-	10	-	ns
Source-drain	n diode FET1 and FET2	I	1		1		
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.83	1.2	V
t _{rr}	reverse recovery time	I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	16.8	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C		-	9.1	-	nC



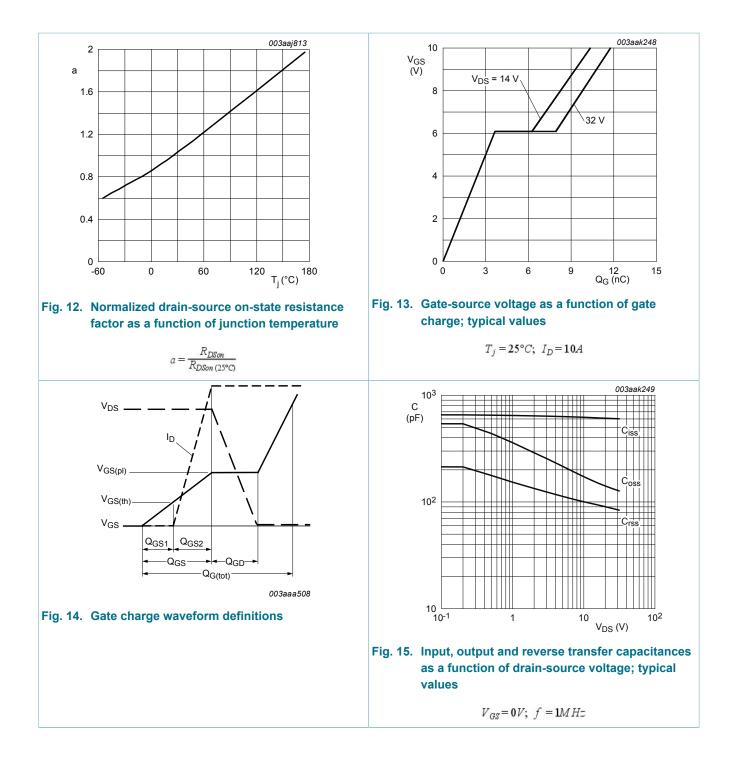
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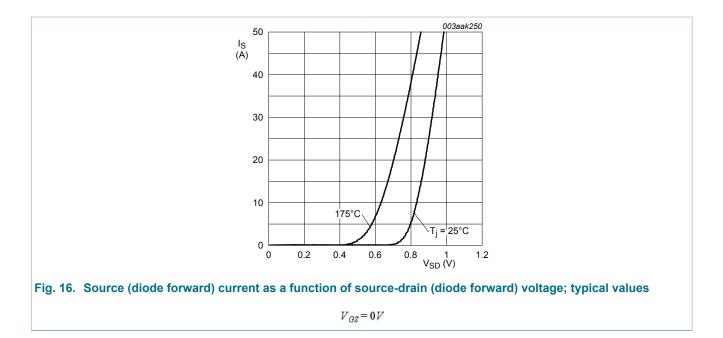
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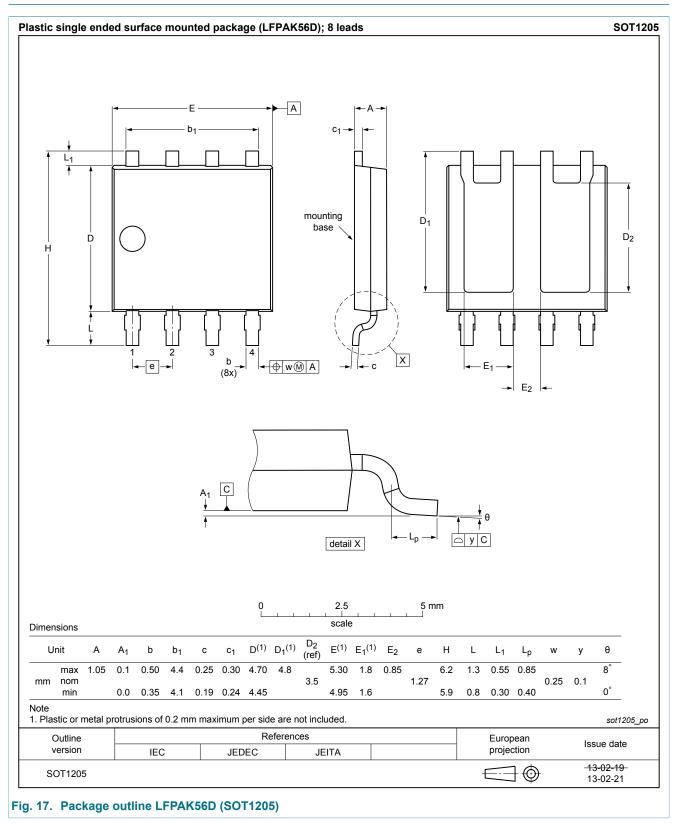
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11. Package outline



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Product data sheet

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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